# 2SC5993

## Silicon NPN epitaxial planar type

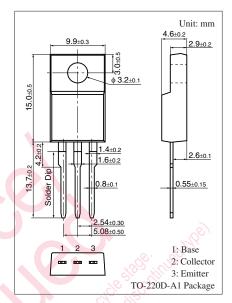
For power amplification For TV VM circuit

#### ■ Features

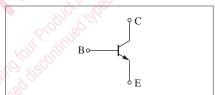
- Satisfactory linearity of forward current transfer ratio h<sub>FE</sub>
- High transition frequency (f<sub>T</sub>)
- Full-pack package which can be installed to the heat sink with one screw.

### ■ Absolute Maximum Ratings $T_C = 25$ °C

| Parameter                          | Symbol               | Rating      | Unit |  |
|------------------------------------|----------------------|-------------|------|--|
| Collector-base voltage (Emitter op | en) V <sub>CBO</sub> | 180         | V    |  |
| Collector-emitter voltage (Base op | en) V <sub>CEO</sub> | 180         | V    |  |
| Emitter-base voltage (Collector op | en) V <sub>EBO</sub> | 6           | V    |  |
| Collector current                  | $I_{C}$              | 1.5         | A    |  |
| Peak collector current             | I <sub>CP</sub>      | 3           | A    |  |
| Collector power dissipation        | P <sub>C</sub>       | 20          | W    |  |
| $T_a = 25$                         | 5°C                  | 2.0         |      |  |
| Junction temperature               | $T_{j}$              | 150         | °C   |  |
| Storage temperature                | T <sub>stg</sub>     | -55 to +150 | °C   |  |



#### Internal Connection



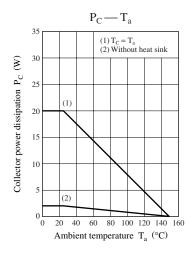
### ■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

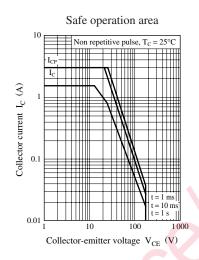
| Parameter                                    | Symbol               | Conditions   | Min | Тур | Max | Unit |
|--|----------------------|--|-----|-----|-----|------|
| Collector-emitter voltage (Base open)        | V <sub>CEO</sub>     | $I_C = 10 \text{ mA}, I_B = 0$                                     | 180 |     |     | V    |
| Collector-base cutoff current (Emitter open) | I <sub>CBO</sub>     | $V_{CB} = 180 \text{ V}, I_E = 0$                                  |     |     | 100 | μΑ   |
| Emitter-base cutoff current (Collector open) | I <sub>EBO</sub>     | $V_{EB} = 6 \text{ V}, I_{C} = 0$                                  |     |     | 100 | μΑ   |
| Forward current transfer ratio *             | h <sub>FE</sub>      | $V_{CE} = 5 \text{ V}, I_{C} = 0.1 \text{ A}$                      | 60  |     | 240 | _    |
| Collector-emitter saturation voltage         | V <sub>CE(sat)</sub> | $I_C = 1 A, I_B = 0.1 A$   |     |     | 0.5 | V    |
| Transition frequency                         | $f_T$                | $V_{CE} = 10 \text{ V}, I_{C} = 0.2 \text{ A}, f = 10 \text{ MHz}$ |     | 130 |     | MHz  |
| Collector output capacitance                 | C <sub>ob</sub>      | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$                |     | 10  |     | pF   |
| (Common base, input open circuited)          |                      |  |     |     |     |      |
| Turn-on time                                 | t <sub>on</sub>      | $I_C = 0.4$ A, Resistance loaded                                   |     | 0.1 |     | μs   |
| Storage time                                 | t <sub>stg</sub>     | $I_{B1} = 0.04 \text{ A}, I_{B2} = -0.04 \text{ A}$                |     | 1.5 |     | μs   |
| Fall time                                    | t <sub>f</sub>       | $V_{CC} = 100 \text{ V}$   |     | 0.1 |     | μs   |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

#### 2. \*: Rank classification

| Rank     | Q         | Р          |  |  |
|----------|-----------|------------|--|--|
| $h_{FE}$ | 60 to 140 | 120 to 240 |  |  |





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